



MACRONIX
INTERNATIONAL Co., LTD.

MX23K64GL0

64G-BIT ROM TYPE GAME CARD MEMORY DATASHEET

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1. FEATURES

- Voltage Supply
 - VCC : 3.1V
 - VCCIO : 1.8V
- Organization
 - 8192M x 8bit
- Read Operation
 - Page Size: 512 Byte
 - Read Cycle Time: 19.2ns (Min.)
- Current
 - Read: 190mA
 - Standby: 600uA
- Command/Address/Data Multiplexed Port
- Security Embedded
- Power On Reset Function
- Package: LGA 16L

2. GENERAL DESCRIPTION

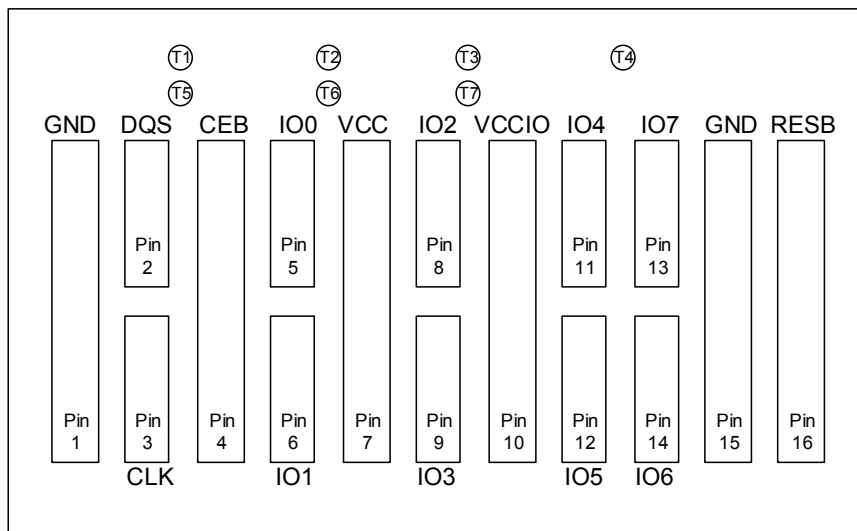
The MX23K64GL0 is a 64Gbit factory pre-programmed MLC NAND (ROM TYPE) with 3.1V and IO 1.8V.

It is a bidirectional device, which utilizes the 8 bit multiplexed I/O bus for command, address, and data inputs/outputs.

Simple design structure makes the cost of the device competitive over the other types of code-storage memory IC.

3. PIN CONFIGURATIONS

LGA 16L



4. PIN DESCRIPTION

SYMBOL	PIN#	TYPE	DESCRIPTION
GND	1, 15	I	Ground
DQS	2	O	Feedback Clock of CLK (Data Strobe Signal)
CLK	3	I	Clock Signal
CEB	4	I	Chip Enable Signal 0 : Enable 1 : Disable
IO0	5	I/O	Command/Address/Data/Ready/Busy Multiplexed I/O Port
IO1	6	I/O	Command/Address/Data/Wait Multiplexed I/O Port
IO2~IO7	8, 9, 11~14	I/O	Command/Address/Data Multiplexed I/O Port
VCC	7	I	Power (3.1V, for Internal Core)
VCCIO	10	I	Power (1.8V, for I/O)
RESB	16	I	Reset Signal 0 : Device Reset
T1~T7	-	-	Test Pins, no connection

5. BLOCK DIAGRAM

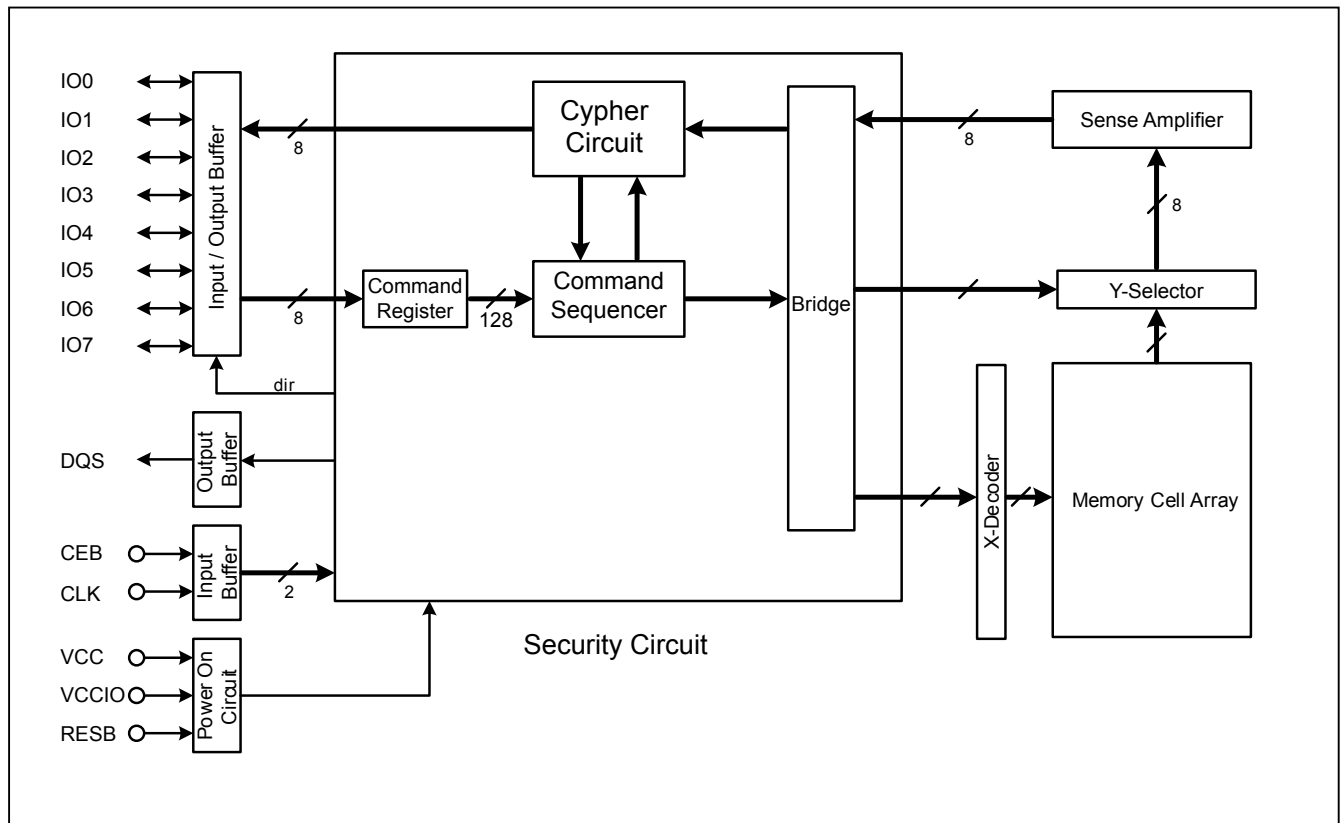


Figure 1. Block Diagram

6. CARD STATUS DEFINITION

Table 1. Card Status

	DESCRIPTION
bit0	CRC Error Flag 0: No Error 1: Error
bit1	0
bit2	Fatal Error Flag 0: No Error 1: Error
bit3	Refresh Request Flag 0: Not Refresh Request 1: Refresh Request
bit4-7	0h

7. ID DEFINITION

Table 2. RD_ID1/t1RD_ID1

ID1	VALUES	DESCRIPTION
ID1_0	C2h	Maker Code
ID1_1	E0h	Memory Size
ID1_2	02h	Option1
ID1_3	21h (Note1)	Memory Type

Note1: bit7 Reserved = 0
bit6 Reserved = 0
bit5 0: tRB_5 ≤ 100us
 1: tRB_5 > 100us
bit4 Reserved = 0
bit3 0: ROM Type
 1: R/W Type
bit2 Reserved = 0
bit[1:0] 00: Reserved
 01: T1
 10: T2
 11: Reserved

Note2: tRB_5 means tRB_N5 and tRB_S5.

Table 3. RD_ID2/t1RD_ID2

ID2	VALUES	DESCRIPTION
ID2_0	02h	Option1
ID2_1	00h	Option2
ID2_2	00h	Option3
ID2_3	00h	Option4

Table 4. RD_ID3/t1RD_ID3

ID3	VALUES	DESCRIPTION
ID3_0	00h	Option1
ID3_1	00h	Option2
ID3_2	00h	Option3
ID3_3	00h	Option4

8. RES DEFINITION**Table 5. RD_SELF_REFRESH**

RES	VALUES	DESCRIPTION
RES0	00h (Note1)	Self Refresh Status
	01h (Note2)	
RES1	00h	Response1
RES2	00h	Response2
RES3	00h	Response3

Note 1: Unnecessary

Note 2: Self Refresh Start

Table 6. RD_REFRESH_STATUS

RES	VALUES	DESCRIPTION
RES0	00h (Note1)	Self Refresh Status
	01h (Note2)	
	03h (Note3)	
	FFh (Note4)	
RES1	00h ~ 0Fh (Note5)	Self Refresh Sum Total
RES2	00h (Note6)	Self Refresh Error
	01h (Note7)	
RES3	00h	Response1

Note 1: Finish (No Error)

Note 2: Executing

Note 3: Finish (Error)

Note 4: Non-Execute

Note 5: Success Count (RES1 ≥ 0Fh is 0Fh)

Note 6: No Error

Note 7: Error

9. ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS
Power Supply Voltage1	V_{CC}	-0.5V to 4.6V
Power Supply Voltage2	V_{CCIO}	-0.5V to 2.5V
Input Voltage	V_{IN}	-0.3V to V_{CCIO} +0.3V (Note1)
Output Voltage	V_{OUT}	-0.3V to V_{CCIO} +0.3V (Note1)
Ambient Operating Temperature	T_{OPR}	0°C to 60°C
Storage Temperature	T_{STG}	-25°C to 85°C

Note1:

Minimum DC voltage on input or I/O pins is -0.3V. During voltage transitions, inputs may undershoot GND to -1.3V for periods of up to 20ns.

Maximum DC voltage on input or I/O pins is V_{CCIO} +0.3V. During voltage transitions, inputs may overshoot V_{CCIO} to V_{CCIO} +2.0V for periods of up to 20ns.

10. RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Operating Temperature	T_A	0	25	60	°C
Power Supply Voltage	V_{CC}	2.8	3.1	3.4	V
IO Power Supply Voltage	V_{CCIO}	1.62	1.8	1.98	V

11. DC CHARACTERISTICS

Table 7. DC Characteristics ($T_A = 0 \sim 60^\circ\text{C}$, $V_{CC} = 2.8 \sim 3.4\text{V}$, $V_{CCIO} = 1.62 \sim 1.98\text{V}$)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	MAX.	UNIT
Input High Voltage	V_{IH}	-		$0.75 * V_{CCIO}$	$V_{CCIO} + 0.3$	V
Input Low Voltage	V_{IL}	-		-0.3	$0.3 * V_{CCIO}$	V
Schmitt Trigger Input (L to H) (CLK, CEB)	V_{t+}	-		-	$0.7 * V_{CCIO}$	V
Schmitt Trigger Input (H to L) (CLK, CEB)	V_{t-}	-		$0.3 * V_{CCIO}$	-	V
Schmitt Trigger Hysteresis Voltage (CLK, CEB)	$(\Delta)V_t$	-		0.15	-	V
Output High Voltage	V_{OH}	$I_{OH} = -400\mu\text{A}$		$0.85 * V_{CCIO}$	-	V
Output Low Voltage	V_{OL}	$I_{OL} = 1.6\text{mA}$		-	$0.1 * V_{CCIO}$	V
Operating Current1	I_{CC1-1}	$t_{WC} = 20\text{ns}$		-	190	mA
	I_{CC1-2}	$t_{WC} = 40\text{ns}$		-	140	mA
Operating Current2	$I_{CCIO2-1}$	$t_{WC} = 20\text{ns}$		-	30	mA
	$I_{CCIO2-2}$	$t_{WC} = 40\text{ns}$		-	20	mA
Standby Current1	I_{CC_STB1}	CEB = $V_{CCIO} - 0.2\text{V}$, IO = $V_{CCIO} - 0.2\text{V}$ or 0.2V , CLK = $V_{CCIO} - 0.2\text{V}$	$T_A = 25^\circ\text{C}$	-	600	μA
			$T_A = 60^\circ\text{C}$	-	1000	μA
	I_{CCIO_STB1}	CEB = $V_{CCIO} - 0.2\text{V}$, IO = $V_{CCIO} - 0.2\text{V}$ or 0.2V , CLK = $V_{CCIO} - 0.2\text{V}$	$T_A = 25^\circ\text{C}$	-	100	μA
			$T_A = 60^\circ\text{C}$	-	200	μA
Standby Current2	I_{CC_STB2}	CEB = $V_{CCIO} - 0.2\text{V}$, IO = $V_{CCIO} - 0.2\text{V}$ or 0.2V , $t_{WC} = 20\text{ns}$ (Duty 50%)	$T_A = 25^\circ\text{C}$	-	600	μA
			$T_A = 60^\circ\text{C}$	-	1000	μA
	I_{CCIO_STB2}	CEB = $V_{CCIO} - 0.2\text{V}$, IO = $V_{CCIO} - 0.2\text{V}$ or 0.2V , $t_{WC} = 20\text{ns}$ (Duty 50%)	$T_A = 25^\circ\text{C}$	-	100	μA
			$T_A = 60^\circ\text{C}$	-	200	μA
Input Leakage Current	I_{LI}	$V_{IN} = 0 \text{ to } V_{CC}(\text{max})$		-	± 10	μA
Output Leakage Current	I_{LO}	$V_{OUT} = 0 \text{ to } V_{CC}(\text{max})$		-	± 10	μA

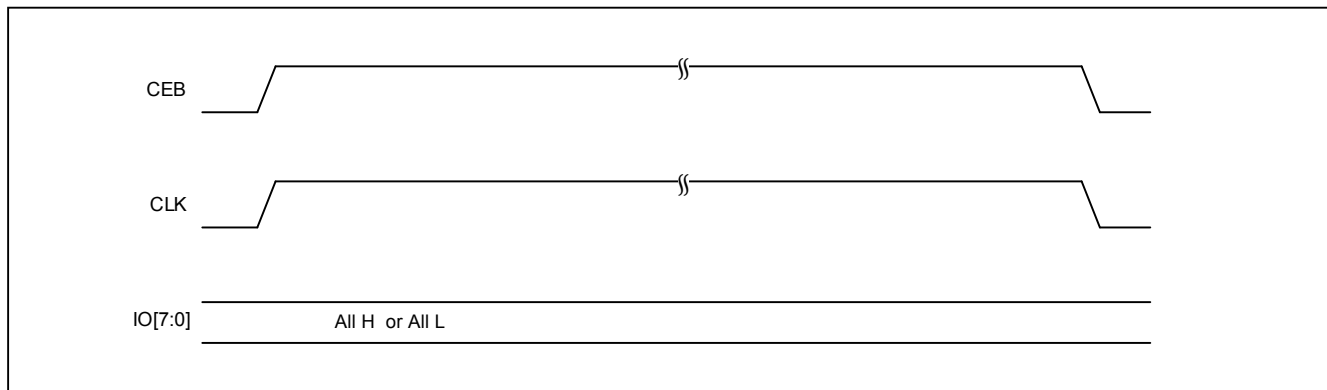


Figure 2. Standby Current (ISTB1)

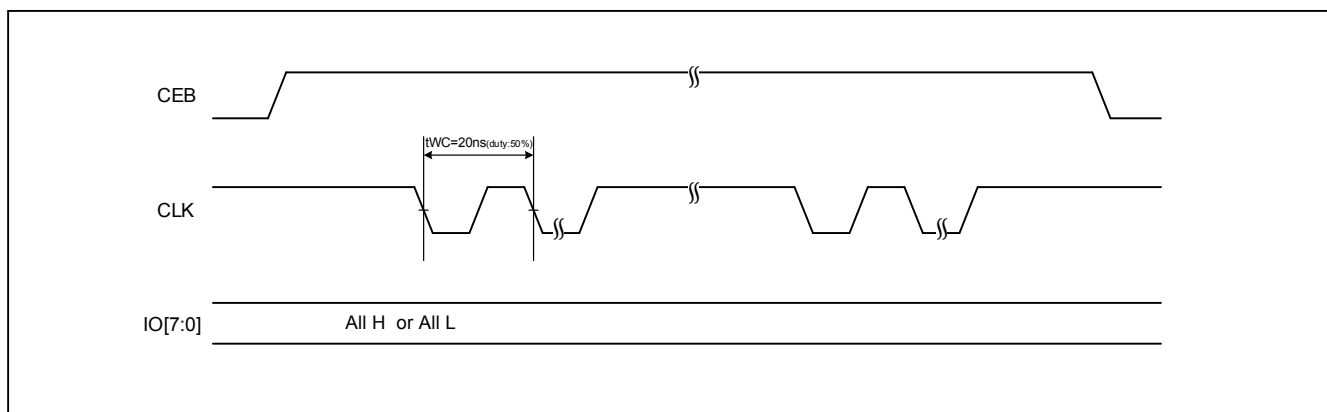


Figure 3. Standby Current (ISTB2)

12. CAPACITANCE

Table 8. Capacitance ($T_A = 0\sim 60^\circ\text{C}$, $V_{CC} = 2.8\sim 3.4\text{V}$, $V_{CCIO} = 1.62\sim 1.98\text{V}$, $f = 1.0\text{MHz}$)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	MAX.	UNIT
Output Capacitance	C_{OUT}	$V_{OUT} = 0\text{V}$	-	15	pF
Input Capacitance	C_{IN}	$V_{IN} = 0\text{V}$	-	15	pF

13. AC CHARACTERISTICS

Table 9. AC TEST CONDITION

PARAMETER	TEST CONDITIONS
Input Pulse Level	$V_{CCIO} * 0.1$ to $V_{CCIO} * 0.9$
Input Rise and Fall Times	3ns
Input Timing Levels (CLK)	$V_{CCIO} * 0.5$
Input Timing Levels (CEB, IO, RESB)	$V_{CCIO} * 0.3$ to $V_{CCIO} * 0.7$
Output Timing Levels	0.45V to $V_{CCIO} - 0.45\text{V}$
Output Load	30pF

Note1: $V_{CCIO} = 1.62\text{V}\sim 1.98\text{V}$

Table 10. AC Characteristics (50MHz, $T_A = 0 \sim 60^\circ\text{C}$, $V_{CC} = 2.8 \sim 3.4\text{V}$, $V_{CCIO} = 1.62 \sim 1.98\text{V}$)

PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNIT
CLK Cycle Time		tWC	19.2	20	-	ns
CLK High Pulse Width		tWH	9	10	-	ns
CLK Low Pulse Width		tWL	9	10	-	ns
CEB Setup Time		tCS	90	-	-	ns
CEB Hold Time		tCH	60	-	-	ns
CEB High Pulse Width		tCEPH	300	-	-	ns
Data Setup Time		tDS	3	-	-	ns
Data Hold Time		tDH	4	-	-	ns
Data Valid Time		tDV	0	-	-	ns
CLK Access Time (Note4)		tREA	0	-	40	ns
DQS Delay Time		tDQSD	0	-	40	ns
DQS Cycle Time		tSWC	19.2	-	-	ns
DQS High Pulse Width		tSWH	5	-	-	ns
DQS Low Pulse Width		tSWL	5	-	-	ns
DQS Data Setup Time		tSDS	5	-	-	ns
DQS Data Hold Time		tSDH	5	-	-	ns
Ready/Busy1	RD_ID1	tRB_N1	2			cycle
	RD_ID2	tRB_N2	2			cycle
	RD_ID3	tRB_N3	2			cycle
	CHG_INIT	tRB_N4	2			cycle
	RD_PAGE	tRB_N5	-	-	30	ms
	RD_SELF_REFRESH (Note3)	tRB_N6	-	-	300	us
	RD_REFRESH_STATUS	tRB_N7	6			cycle
	iRD_INIT	tRB_I1	-	-	30	ms
	iSET_INIT1	tRB_I2	314			cycle
	iSET_GEN_RAND	tRB_I3	-	-	400	us
	iSET_INIT2	tRB_I4	314			cycle
	t1RD_ID1	tRB_S1	18	-	24	cycle
	t1RD_ID2	tRB_S2	18	-	24	cycle
	t1RD_ID3	tRB_S3	18	-	24	cycle
	t1RD_UID	tRB_S4	-	-	400	us
	t1RD_PAGE	tRB_S5	-	-	10	ms
	t1RD_REFRESH	tRB_S6	26cycle	-	600	ms
	t1RD_SET_KEY	tRB_S7	314			cycle
Ready/Busy2	RD_PAGE	tRB2_N1	2cycle	-	1.5	ms
	t1RD_PAGE	tRB2_S1	2cycle	-	1.5	ms
CEB High to Output Hi-Z Time (Note1)		tCHZ	-	-	30	ns
Output to Hi-Z Time (Note1)		tSDHZ	-	-	15	ns
Latency1		tHZ1	2			cycle
Latency2		tHZ2	1			cycle
Latency3		tHZ3	1			cycle
Active to Standby Time (Note1)		tAST	-	-	15	us

Note1: This spec is guaranteed with design specification, not tested.

Note2: tRB_* and tRB2_* are based on Wait=0cycle.

Note3: It needs to issue RD_PAGE before RD_SELF_REFRESH at least once.

Note4: Data always starts to output after CLK rising edge.

Table 11. AC Characteristics (25MHz, T_A = 0~60°C, V_{CC} = 2.8~3.4V, V_{CCIO} = 1.62~1.98V)

PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNIT
CLK Cycle Time		tWC	38	40	-	ns
CLK High Pulse Width		tWH	18	20	-	ns
CLK Low Pulse Width		tWL	18	20	-	ns
CEB Setup Time		tCS	120	-	-	ns
CEB Hold Time		tCH	165	-	-	ns
CEB High Pulse Width		tCEPH	300	-	-	ns
Data Setup Time		tDS	15	-	-	ns
Data Hold Time		tDH	4	-	-	ns
Data Valid Time		tDV	0	-	-	ns
CLK Access Time (Note4)		tREA	0	-	27	ns
Ready/Busy1	RD_ID1	tRB_N1	2			cycle
	RD_ID2	tRB_N2	2			cycle
	RD_ID3	tRB_N3	2			cycle
	CHG_INIT	tRB_N4	2			cycle
	RD_PAGE	tRB_N5	-	-	30	ms
	RD_SELF_REFRESH (Note3)	tRB_N6	-	-	300	us
	RD_REFRESH_STATUS	tRB_N7	6			cycle
	iRD_INIT	tRB_I1	-	-	30	ms
	iSET_INIT1	tRB_I2	314			cycle
	iSET_GEN_RAND	tRB_I3	-	-	400	us
	iSET_INIT2	tRB_I4	314			cycle
	t1RD_ID1	tRB_S1	18	-	24	cycle
	t1RD_ID2	tRB_S2	18	-	24	cycle
	t1RD_ID3	tRB_S3	18	-	24	cycle
	t1RD_UID	tRB_S4	-	-	400	us
	t1RD_PAGE	tRB_S5	-	-	10	ms
	t1RD_REFRESH	tRB_S6	26cycle	-	600	ms
	t1RD_SET_KEY	tRB_S7	314			cycle
Ready/Busy2	RD_PAGE	tRB2_N1	2cycle	-	1.5	ms
	t1RD_PAGE	tRB2_S1	2cycle	-	1.5	ms
CEB High to Output Hi-Z Time (Note1)		tCHZ	-	-	30	ns
Output to Hi-Z Time (Note1)		tDHZ	-	-	38	ns
Latency1		tHZ1	2			cycle
Latency2		tHZ2	1			cycle
Latency3		tHZ3	1			cycle
Active to Standby Time (Note1)		tAST	-	-	15	us

Note1: This spec is guaranteed with design specification, not tested.

Note2: tRB_* and tRB2_* are based on Wait=0cycle.

Note3: It needs to issue RD_PAGE before RD_SELF_REFRESH at least once.

Note4: Data always starts to output after CLK rising edge.

Table 12. AC Characteristics for RESB Timing ($T_A = 0 \sim 60^\circ\text{C}$, $V_{CC} = 2.8 \sim 3.4\text{V}$, $V_{CCIO} = 1.62 \sim 1.98\text{V}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
RESB Non-Active Time	tRNA	9	-	-	us
RESB Low Time 1	tRES1	100	-	-	us
RESB High Time 1	tRH1	250	-	-	ms
RESB Setup Time	tRS	100	-	-	ns
RESB Low Time 2	tRES2	1	-	-	us
RESB High Time 2	tRH2	250	-	-	ms

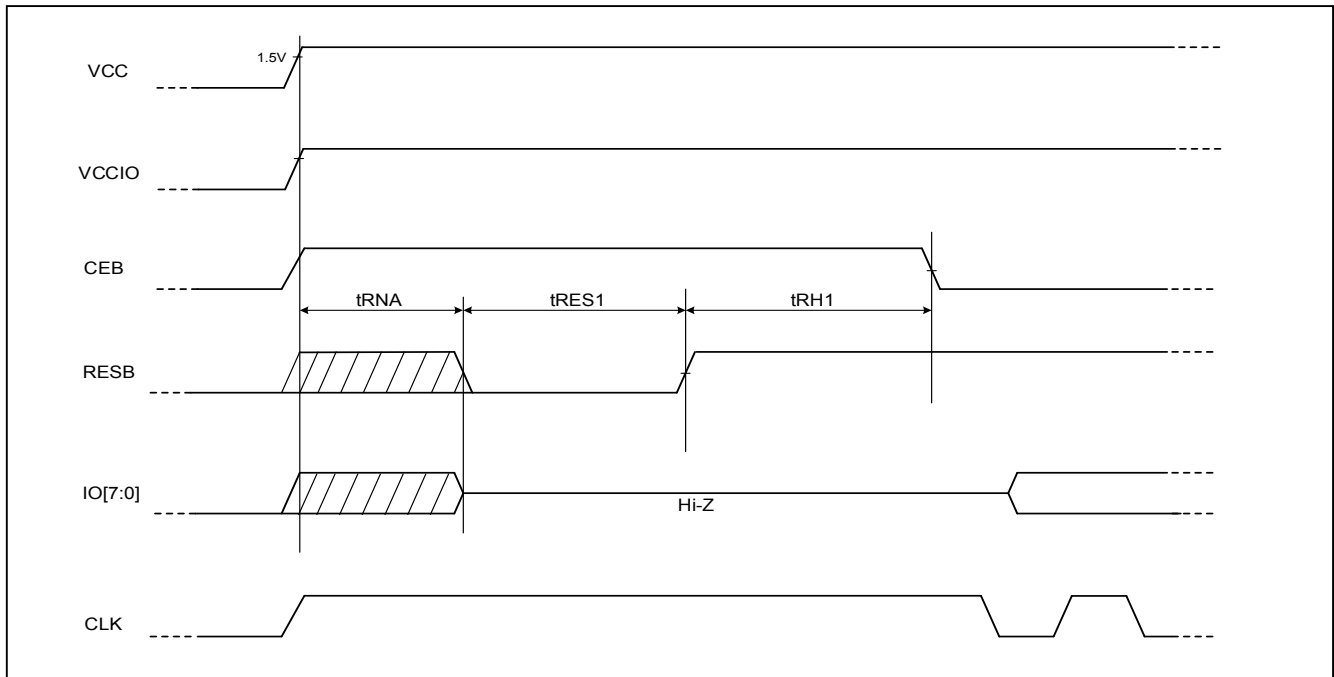
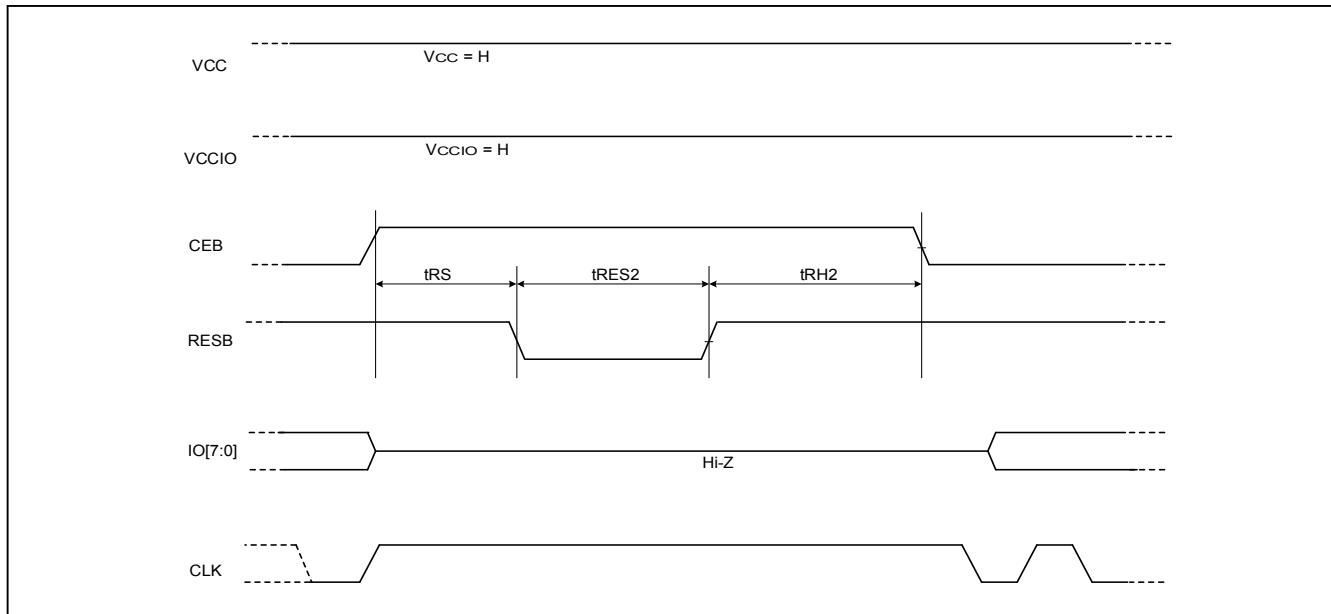


Figure 4. RESB Timing Waveform (Case1)

Note 1: During "RESB=L", IO7~IO0 is Hi-Z.

Note 2: RESB from low to high will triggered POR function during tRH1.

**Figure 5. RESB Timing Waveform (Case 2)**

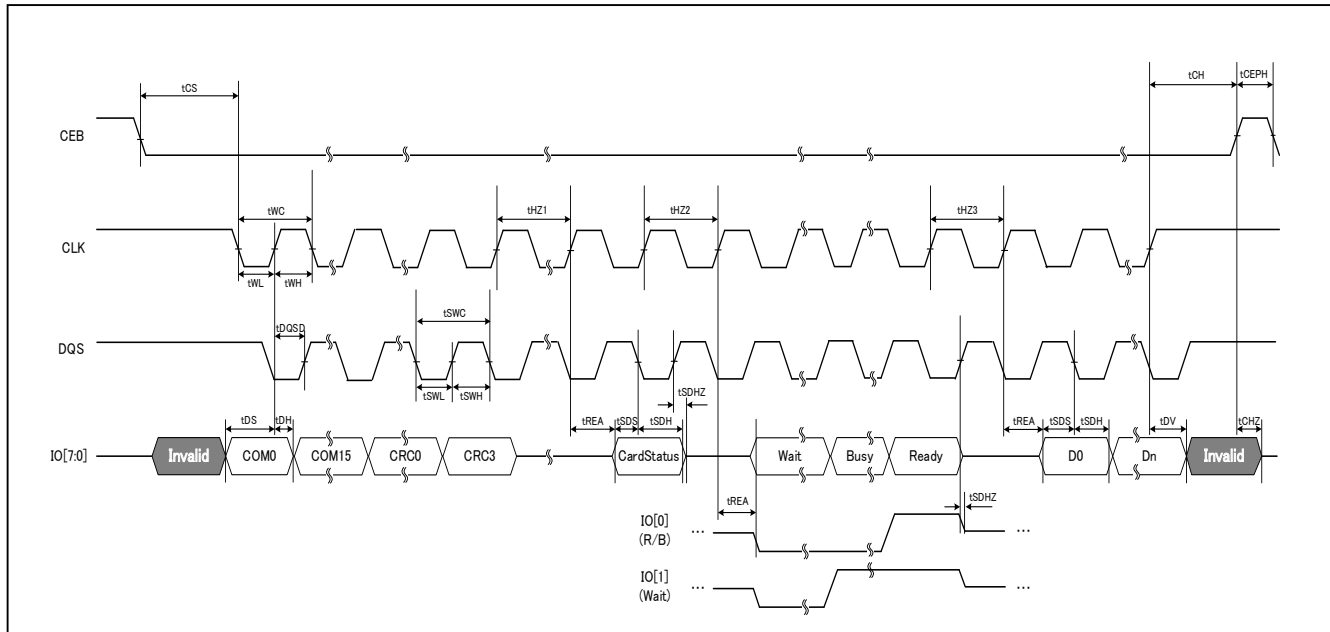


Figure 6. Command Input and Data Output Timing Waveform (Read, 50MHz)

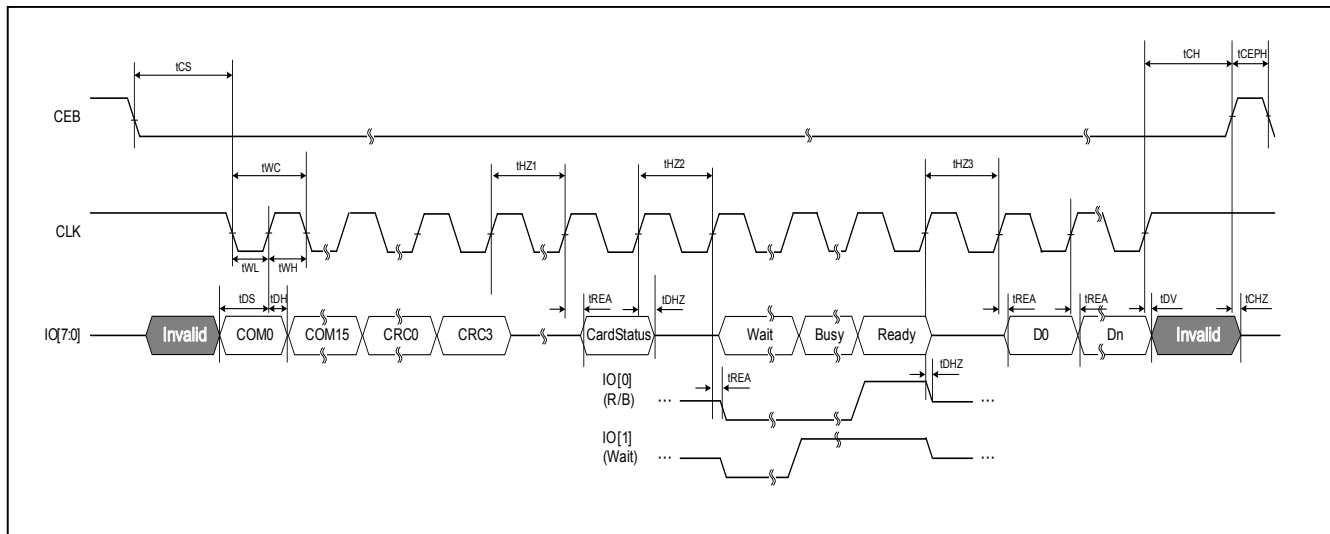


Figure 7. Command Input and Data Output Timing Waveform (Read, 25MHz)

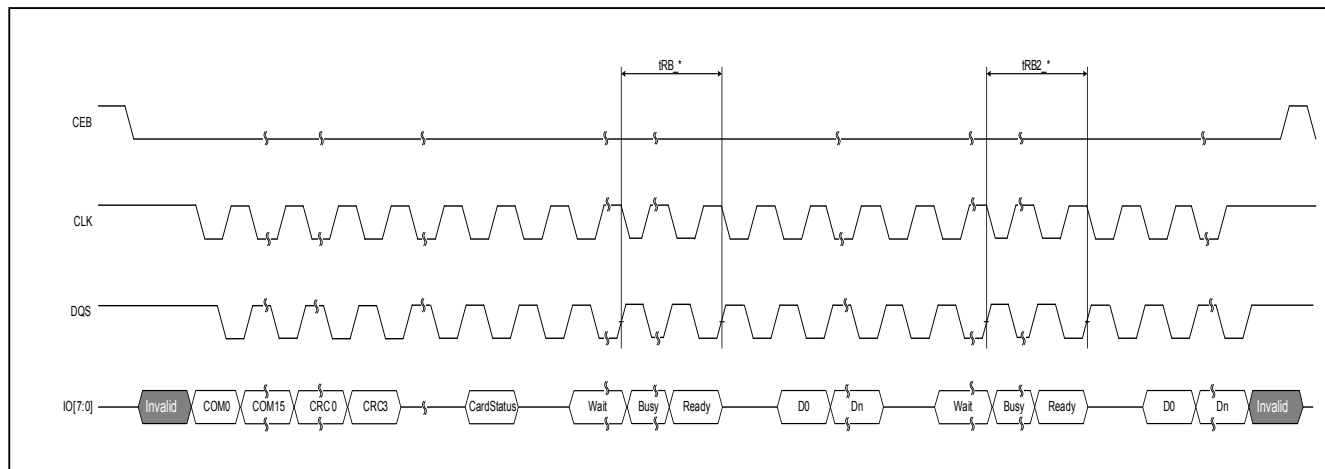


Figure 8. Ready/Busy Timing Waveform (Read, 50MHz)

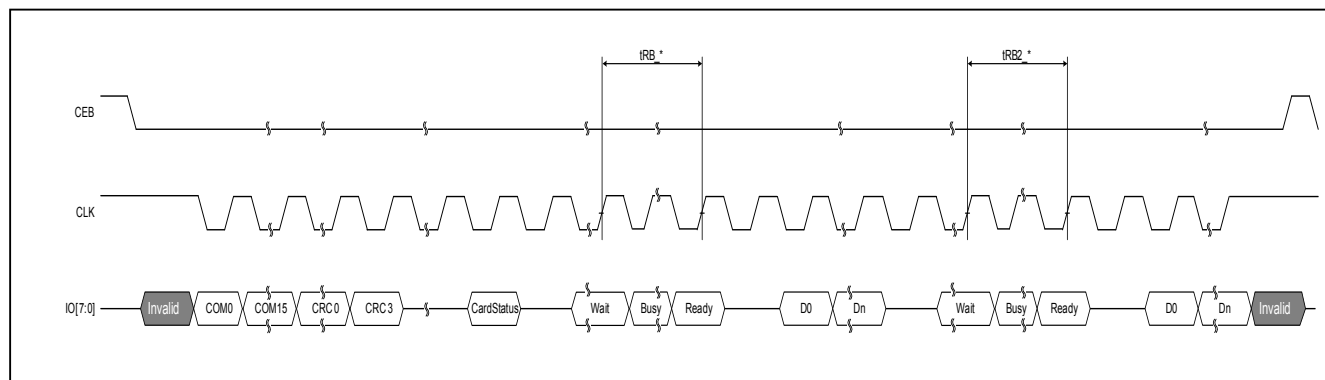


Figure 9. Ready/Busy Timing Waveform (Read, 25MHz)

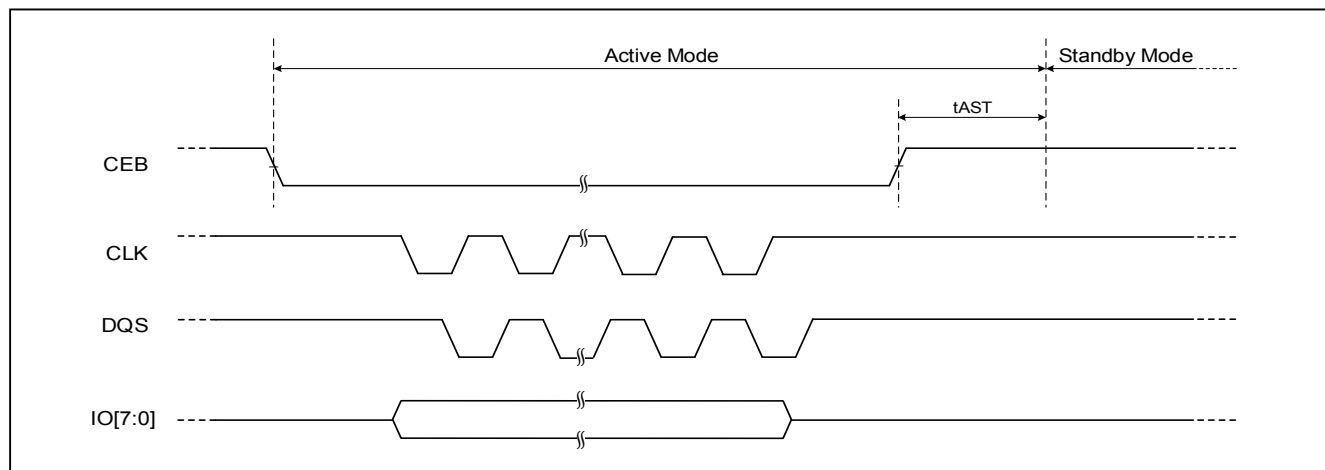
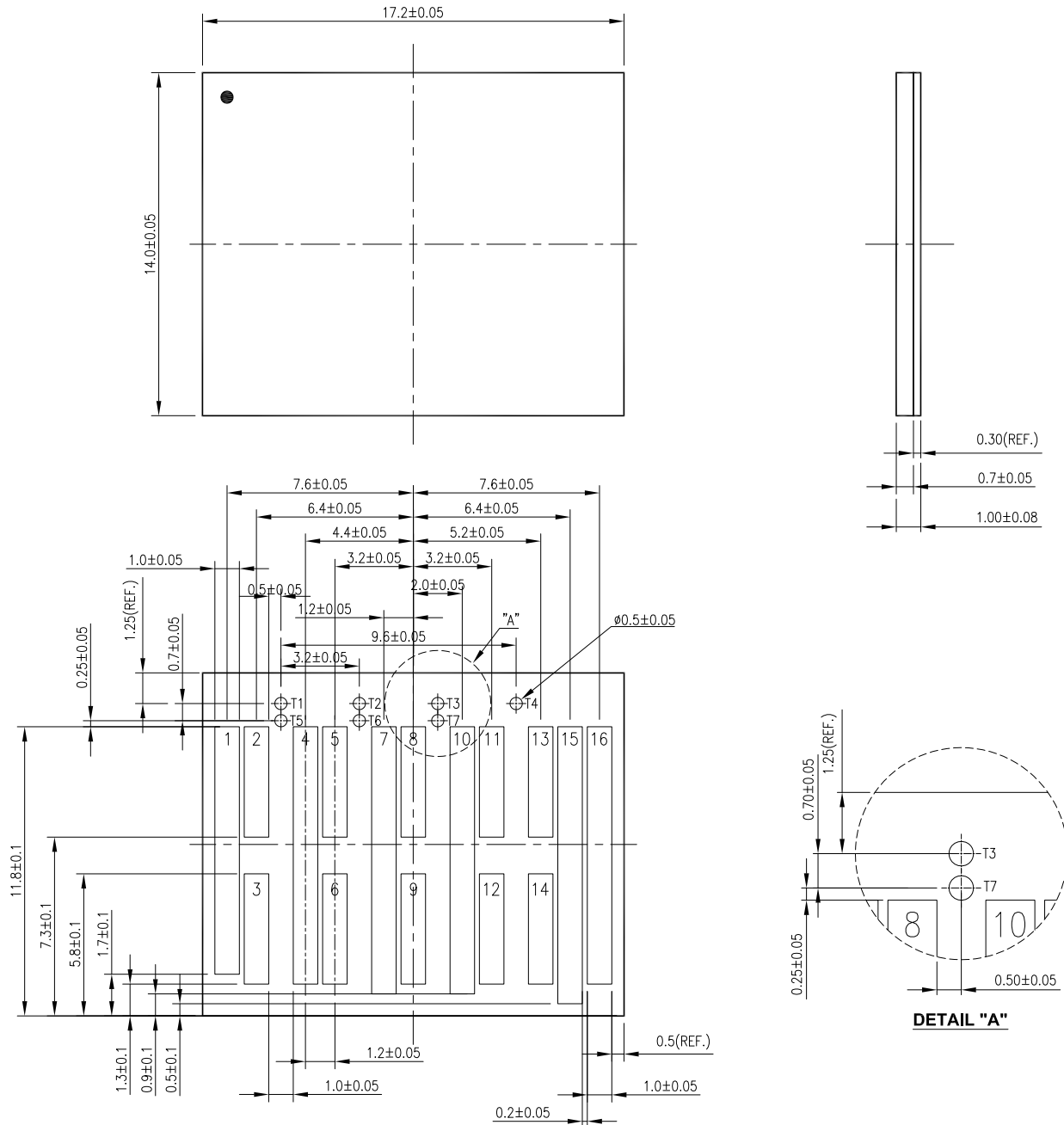


Figure 10. Standby Mode Timing Waveform

14. PACKAGE INFORMATION

Title: Package Outline for LGA 16L (17.2x14.0x1.0MM)



Dimensions Unit: mm

Dwg. No.	Revision	Reference			
		JEDEC	EIAJ		
6110-3202	0				



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MX23K64GL0

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